

ABSTRACT

A memory device is proposed which enables to guarantee the operation of MRAM elements being magnetically shielded against a large external magnetic fields without being affected by an internal leakage magnetic field. The MRAM elements 30 which are shielded by magnetic shield layers 33, 34 are placed at an intermediate region 41 avoiding an edge region 43 and a center region 42 of the magnetic shield layers 33, 34 so that the MRAM element is secured to operate normally without being affected by the internal leakage magnetic field avoiding the edge region 43 where the magnetic shield effect is reduced by the exterior magnetic field, and avoiding the central region 42 where the internal leakage magnetic field is large